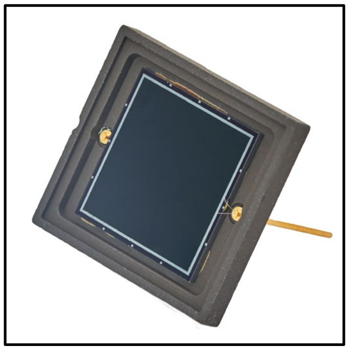
From Deep UV to Mid-IR
OPTO DIODE
An ITW Company

Photodiode 100 mm^2

SXUV100



FEATURES

- Single Active Area
- Detection to 1 nm
- Stable Response after Exposure to EUV/UV Conditions
- Protective Cover Plate[2]

Electro-Optical Characteristics at 25 °C

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	10 mm x 10 mm		100		mm^2
Responsivity	(see graph on next page)				A/W
Shunt Resistance, Rsh	V = ± 10 mV	10			MOhms
Capacitance, C	V_R = 0 V		5	15	nF
Response Time, tr	RL = 50 Ω, V_R = 8 V			6	μ sec

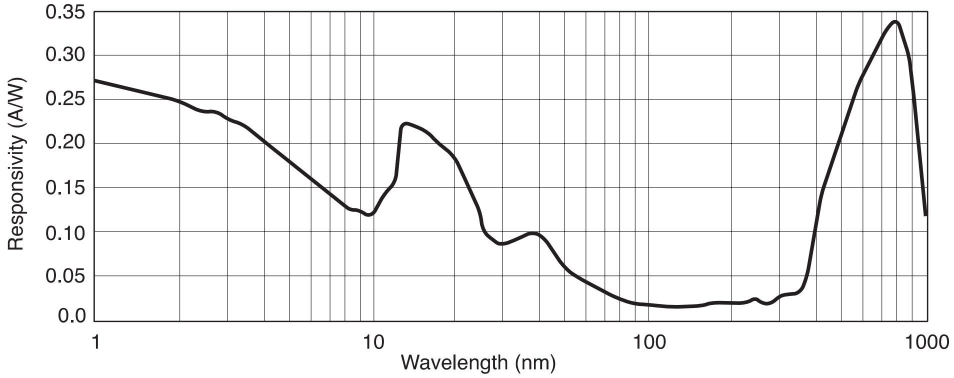
Thermal Parameters

Storage and Operating Temperature Range	Units
Ambient	-10°C to 40°C
Nitrogen or Vacuum	-20°C to 80°C
Lead Soldering Temperature[1]	260°C

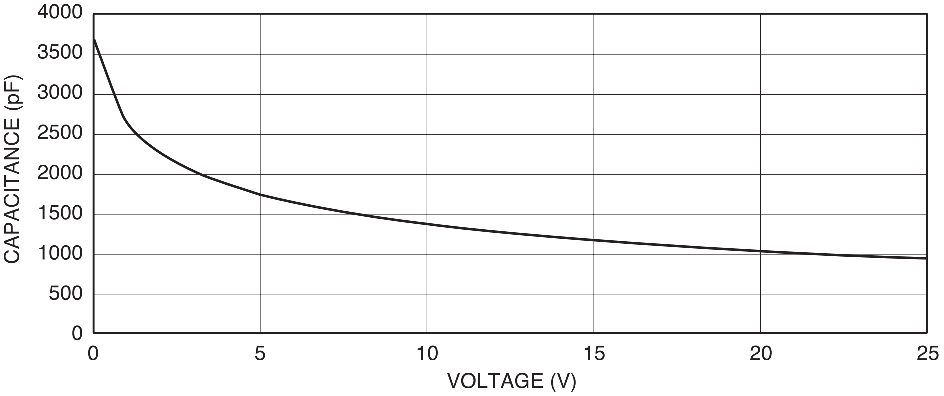
[1] 0.080" from case for 10 seconds.

[2] Shipped with temporary cover to protect the photodiode and wire bonds.
Review the Application Note, “Handling Precautions for AXUV, SXUV, and UVG Detectors”, prior to removing cover.

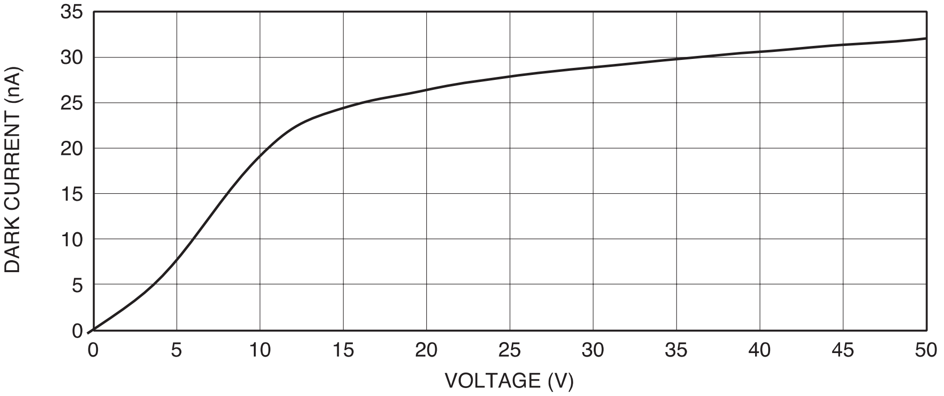
Typical Photon Responsivity



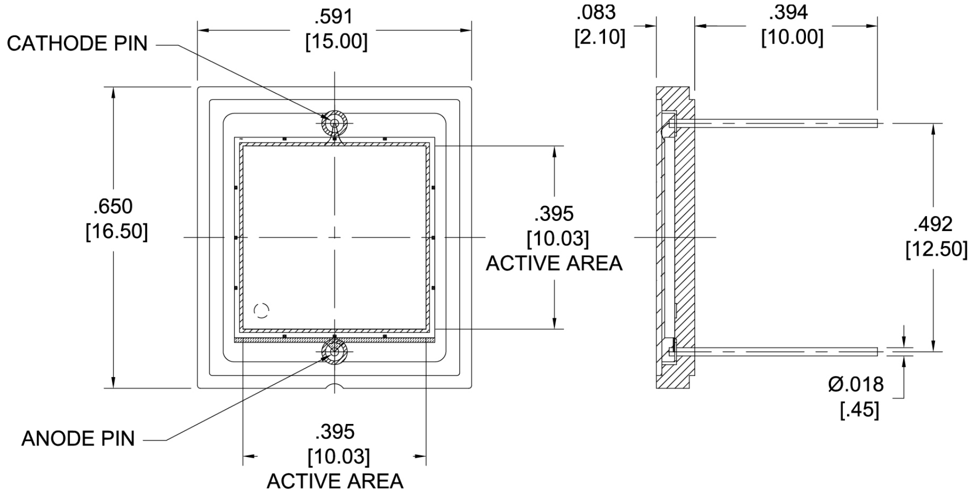
Capacitance vs. Voltage



Dark Current vs. Voltage



Package Information



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.